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MAY 26 2004

Patent

OFFICIALCustomer No.: 31561
Docket No. 11760-US-PA
Application No.: 10/605,360**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Applicant : Lai
Application No. : 10/605,360
Filed : 2003/09/25
For : METHOD FOR FABRICATING A MOSFET AND
REDUCING LINE WIDTH OF GATE STRUCTURE
Art Unit : 2825
Examiner : KESHAVAN, BELUR V

TRANSMITTAL LETTER

002-1-703-872-9306

(Via fax: 14 pages, followed by confirmation copy via courier)

Assistant Commissioner for Patents
Arlington, Virginia 22202

In response to the Office Action dated March 29, 2004, please find the relevant paper in response to paper No. 03182004. Following the fax transmission, a hard copy via courier will also be forwarded to the Office.

Enclosed documents via courier will include:

- ☒ Amendment and Response to Office Action in (7) pages
- ☒ Amended Drawings in (5) pages
- ☒ Fax confirmation report
- ☒ Prepaid return postcard

I believe that no fee is incurred. However, the Commissioner is authorized to charge any fees required in connection with the filing of this paper to account No. 50-2620 (Order No.: 11760-US-PA)

Thank you for your assistance in the subject matter. If you have any questions, please feel free to contact me.

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Patent

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Application No.: 10/605,360

Respectfully Submitted,
JIANQ CHYUN Intellectual Property Office

Date: May 27, 2004

By: Belinda Lee
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Examiner: Keshavan, Belur V.

Group Art Unit: 2825

OFFICIAL

In re PATENT APPLICATION of

Applicants : Lai, Erh-Kun)

Serial No. : 10/605,360)

Filed : September 25, 2003)

For : Method For Fabricating A
MOSFET And Reducing Line
Width Of Gate Structure)AMENDMENT

) Attorney Docket: 11760-US-PA

No fee is believed to be due. However, the Commissioner is authorized to charge any fees required in connection with the filing of this paper to account No. 50-2620 (Order No.: 11760-US-PA)

AMENDMENT AND RESPONSE TO OFFICE ACTION

U.S. Patent and Trademark Office
Commissioner for Patents
2011 South Clark Place
Customer Window, Mail Stop Amendment
Crystal Plaza Two, Lobby, Room 1B03
Arlington, Virginia 22202

Dear Sir:

The Office Action mailed March 29, 2004 has been carefully considered. In response thereto, please enter the following amendments and consider the following

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Application No.: 10/605,360
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remarks.

Amendment

FOR THE SPECIFICATION

[0028] In a preferred embodiment of the present invention, the following steps shown in FIG. 1B' and FIG. 1B'' can be performed between FIG. 1B and FIG. 1C. First, a lining oxide layer 107(not shown) is formed on the surface of the gate structure 105 and the substrate 100, as shown in FIG. 1B'. Then the lining oxide layer 107 is etched back so that only the sidewall of the gate structure 105 has the remaining lining oxide layer 107a thereon, as shown in FIG. 1B''. Then, the step shown in FIG. 1C is performed to form the metal silicide layer 108. Therefore, the metal silicide layer 108 would not be formed on the sidewall of the gate structure 105.